1. General description

NPN/NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PBSS4130PANP. PNP/PNP complement: PBSS5130PAP.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	30	V	
I _C	collector current			-	-	1	Α	
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	2	Α	
Per transistor	Per transistor							
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 0.1 A; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C		-	-	190	mΩ	



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30 V, 1 A NPN/NPN low VCEsat (BISS) transistor

Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		1
3	C2	collector TR2	7 8	(TR1)
4	E2	emitter TR2		
5	B2	base TR2		E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020-6 (SOT1118)	sym140
7	C1	collector TR1	DI 112020-0 (0011110)	
8	C2	collector TR2		

Ordering information

Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
PBSS4130PAN	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1118

Marking 7.

Table 4. **Marking codes**

Type number	Marking code
PBSS4130PAN	2D

Limiting values 8.

Table 5. **Limiting values**

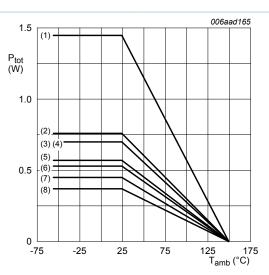
PBSS4130PAN

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit		
Per transistor	Per transistor							
V _{CBO}	collector-base voltage	open emitter		-	30	V		
V _{CEO}	collector-emitter voltage	open base		-	30	V		
V _{EBO}	emitter-base voltage	open collector		-	7	V		
I _C	collector current			-	1	Α		
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α		
I _B	base current			-	0.3	Α		

Symbol	Parameter	Conditions	N	Min	Max	Unit
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
			[5]	-	450	mW
			[6]	-	760	mW
			[7]	-	700	mW
			[8]	-	1450	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
			[5]	-	620	mW
			[6]	-	1040	mW
			[7]	-	960	mW
			[8]	-	2000	mW
T _j	junction temperature		-	-	150	°C
T _{amb}	ambient temperature		-	-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- 6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².



- (1) 4-layer PCB 70 μm, mounting pad for collector 1 cm²
- (2) FR4 PCB 70 µm, mounting pad for collector 1 cm²
- (3) 4-layer PCB 70 µm, standard footprint
- (4) 4-layer PCB 35 μm, mounting pad for collector 1 cm²
- (5) FR4 PCB 35 μm , mounting pad for collector 1 cm²
- (6) 4-layer PCB 35 µm, standard footprint
- (7) FR4 PCB 70 µm, standard footprint
- (8) FR4 PCB 35 µm, standard footprint

Fig. 1. Per transistor: power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transisto	Per transistor							
R _{th(j-a)}	thermal resistance	ermal resistance in free air [1	[1]	-	-	338	K/W	
	from junction to		[2]	-	-	219	K/W	
ambient		[3]	-	-	236	K/W		
		[4]	-	-	179	K/W		
		[6]	[5]	-	-	278	K/W	
			[6]	-	-	164	K/W	
			[7]	-	-	179	K/W	
			[8]	-	-	86	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W	

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device			,				
R _{th(j-a)} thermal resistance	thermal resistance in free air	[1]	-	-	245	K/W	
	from junction to	to	[2]	-	-	160	K/W
ambient		[3]	-	-	171	K/W	
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
		[6]	-	-	120	K/W	
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

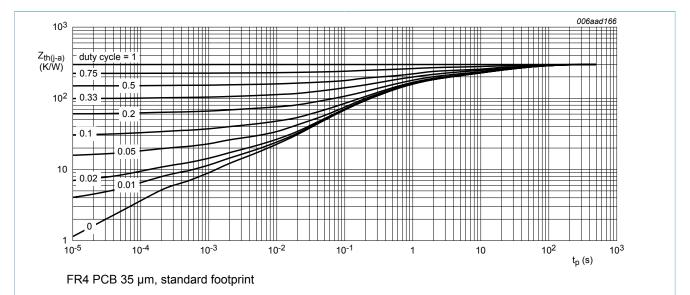


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

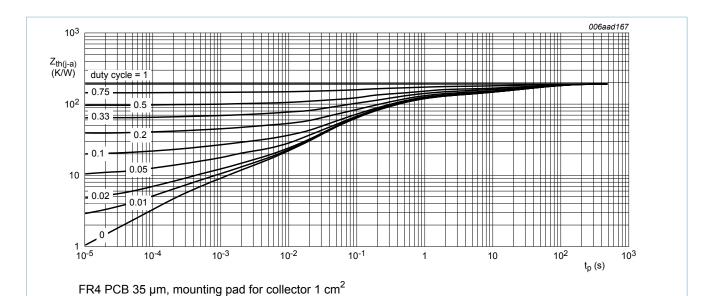


Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

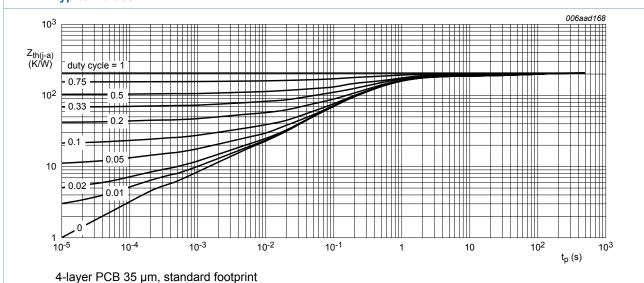


Fig. 4. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

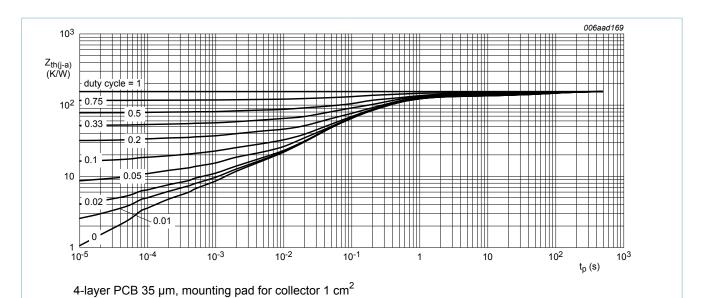


Fig. 5. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

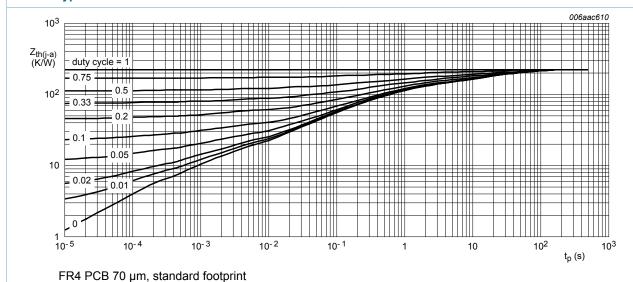


Fig. 6. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

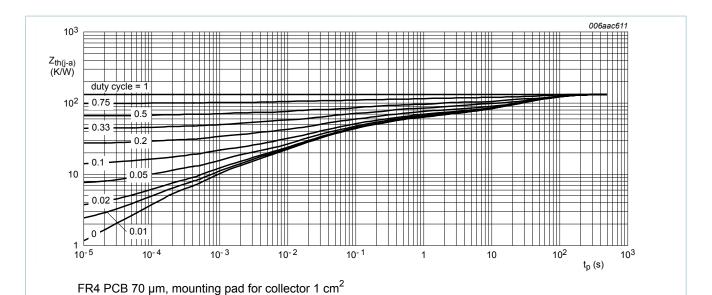


Fig. 7. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

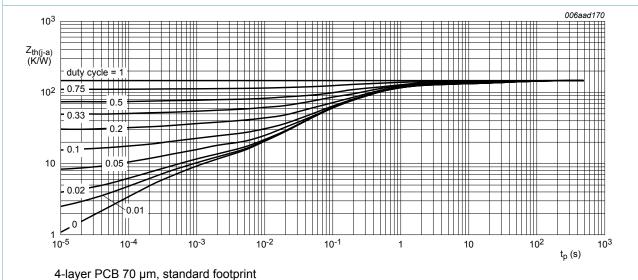
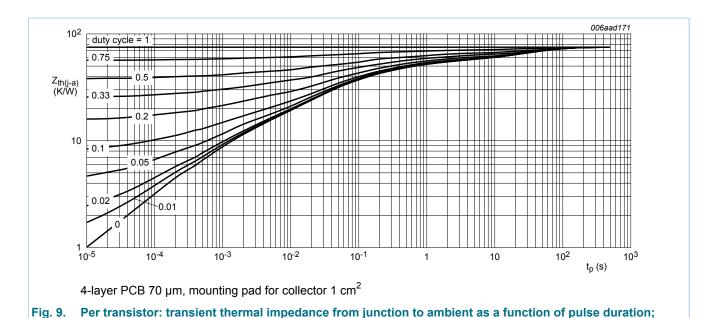


Fig. 8. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values



10. Characteristics

typical values

Table 7. Characteristics

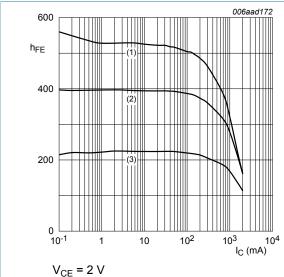
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor		<u> </u>			
I _{CBO}	collector-base cut-off	V _{CB} = 24 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 24 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE} DC current gain	DC current gain	V_{CE} = 2 V; I_{C} = 100 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	240	370	-	
		V_{CE} = 2 V; I_{C} = 500 mA; pulsed; $t_{p} \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	210	320	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	180	270	-	
V _{CEsat}	collector-emitter	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	75	100	mV
sat	saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	155	200	mV
		I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	150	190	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 0.1 A; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	190	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat} base-emitter satur voltage	base-emitter saturation	uration $I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; $T_{amb} = 25 ^{\circ}\text{C}$		-	1	V
	voltage	I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	1.1	V
		I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	0.9	V
t _d	delay time	V _{CC} = 10 V; I _C = 500 mA; I _{Bon} = 25 mA;	-	15	-	ns
t _r	rise time	I_{Boff} = -25 mA; T_{amb} = 25 °C	-	30	-	ns
t _{on}	turn-on time		-	45	-	ns
ts	storage time		-	310	-	ns
t _f	fall time		-	55	-	ns
t _{off}	turn-off time		-	365	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	90	165	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	7.5	10	pF

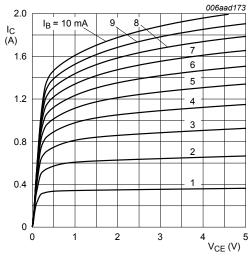


(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

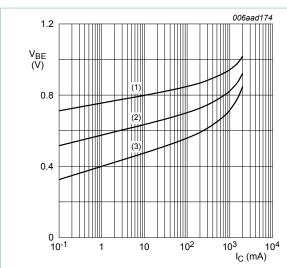
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 10. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 11. Collector current as a function of collectoremitter voltage; typical values

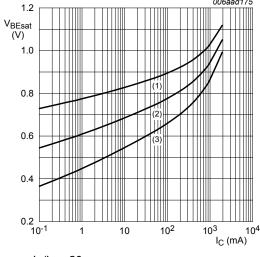


$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C



$$I_{\rm C}/I_{\rm B} = 20$$

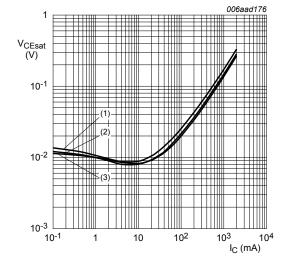
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. Base-emitter voltage as a function of collector current; typical values





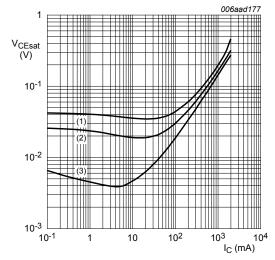
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

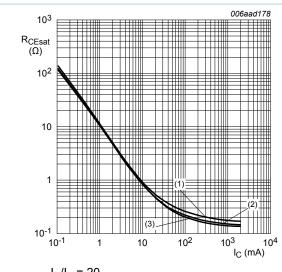
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation voltage as a function of collector current; typical values

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30 V, 1 A NPN/NPN low VCEsat (BISS) transistor



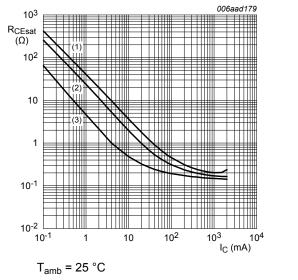
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 16. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

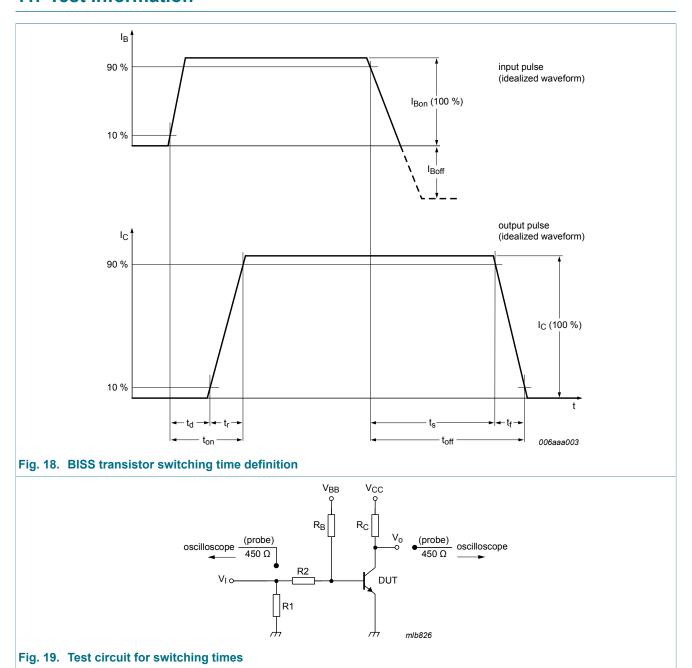
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 17. Collector-emitter saturation resistance as a function of collector current; typical values

Product data sheet

11. Test information



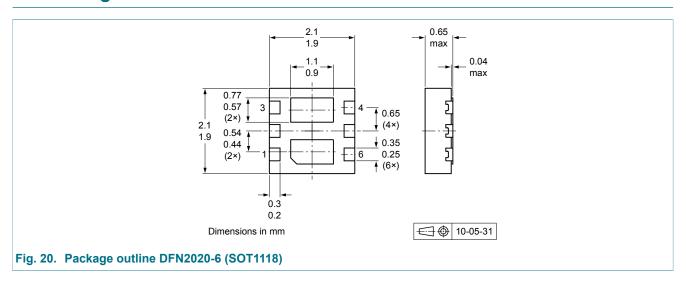
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

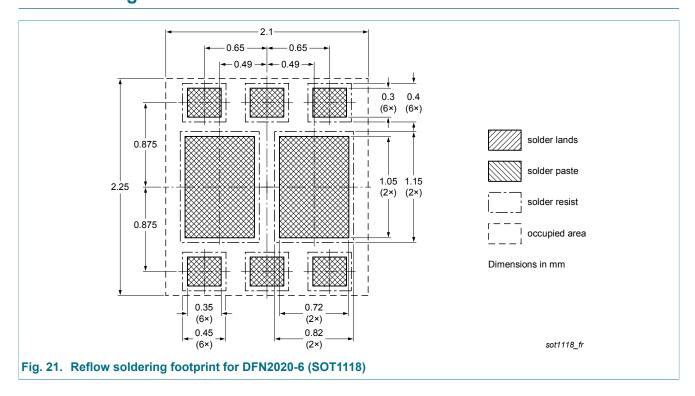
Product data sheet

13 / 17

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4130PAN v.1	20130111	Product data sheet	-	-		

PBSS4130PAN

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Nexperia PBSS4130PAN

30 V, 1 A NPN/NPN low VCEsat (BISS) transistor

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